



TF252

N-Channel JFET 20V, 140 to 350 μ A, 1.4mS, USFP

ON Semiconductor®

<http://onsemi.com>

Features

- High gain : $GV=1.0\text{dB typ}$ ($V_{CC}=2\text{V}$, $R_L=2.2\text{k}\Omega$, $C_{in}=5\text{pF}$, $V_{IN}=10\text{mV}$, $f=1\text{kHz}$)
- Ultrasmall package facilitates miniaturization in end products [1.0mm \times 0.6mm \times 0.27mm (max 0.3mm)]
- Best suited for use in Electret Condenser Microphone for audio equipments and telephones
- Excellent voltage characteristics
- Excellent transient characteristics
- Adoption of FBET process
- Halogen free compliance
- Protection diode in

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

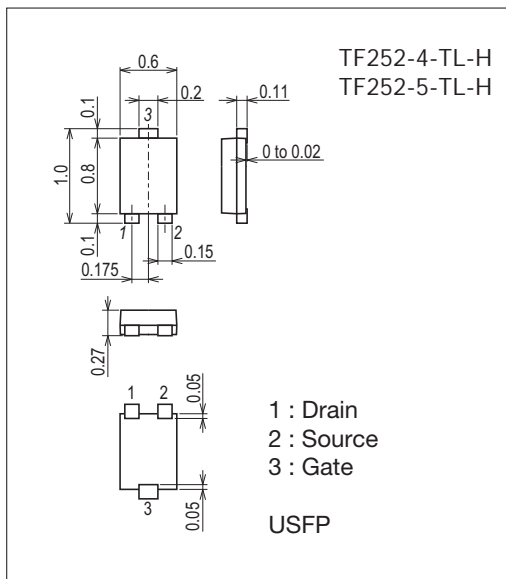
Parameter	Symbol	Conditions	Ratings	Unit
Gate-to-Drain Voltage	V_{GDO}		-20	V
Gate Current	I_G		10	mA
Drain Current	I_D		1	mA
Allowable Power Dissipation	P_D		30	mW
Junction Temperature	T_j		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

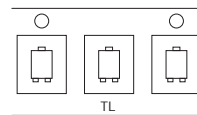
7055-001



Product & Package Information

- Package : USFP
- JEITA, JEDEC : -
- Minimum Packing Quantity : 10,000 pcs./reel

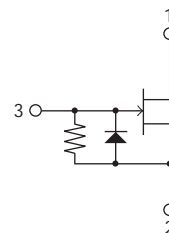
Packing Type: TL



Marking



Electrical Connection



TF252

Electrical Characteristics at Ta=25°C

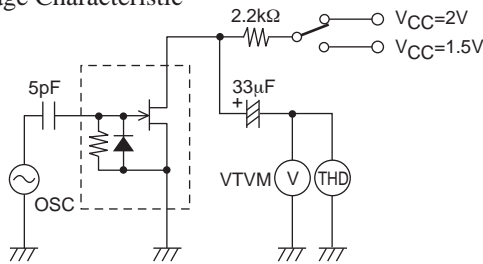
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gate-to-Drain Breakdown Voltage	V(BR)GDO	I _G =-100μA	-20			V
Cutoff Voltage	V _{GS(off)}	V _{DS} =2V, I _D =1μA	-0.1	-0.4	-1.0	V
Drain Current	I _{DSS}	V _{DS} =2V, V _{GS} =0V	140*		350*	μA
Forward Transfer Admittance	y _{fs}	V _{DS} =2V, V _{GS} =0V, f=1kHz	0.8	1.4		mS
Input Capacitance	C _{iss}	V _{DS} =2V, V _{GS} =0V, f=1MHz		3.1		pF
Reverse Transfer Capacitance	C _{rss}			0.95		pF
[Ta=25°C, V _{CC} =2V, R _L =2.2kΩ, C _{in} =5pF, See specified Test Circuit.]						
Voltage Gain	G _V	V _{IN} =10mV, f=1kHz		1.0		dB
Reduced Voltage Characteristic	ΔG _V V	V _{IN} =10mV, f=1kHz, V _{CC} =2.0V → 1.5V		-0.6	-2.0	dB
Frequency Characteristic	ΔG _V f	f=1kHz to 110Hz			-1.0	dB
Total Harmonic Distortion	THD	V _{IN} =30mV, f=1kHz		0.65		%
Output Noise Voltage	V _{NO}	V _{IN} =0V, A curve		-106	-102	dB

* : The TF252 is classified by I_{DSS} as follows : (unit : μA)

Rank	4	5
I _{DSS}	140 to 240	210 to 350

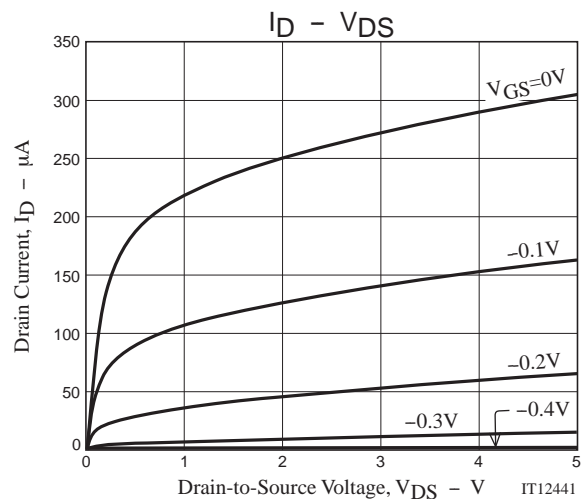
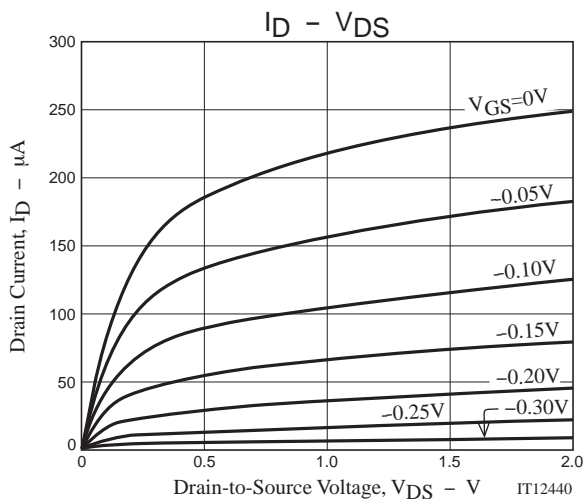
Test Circuit

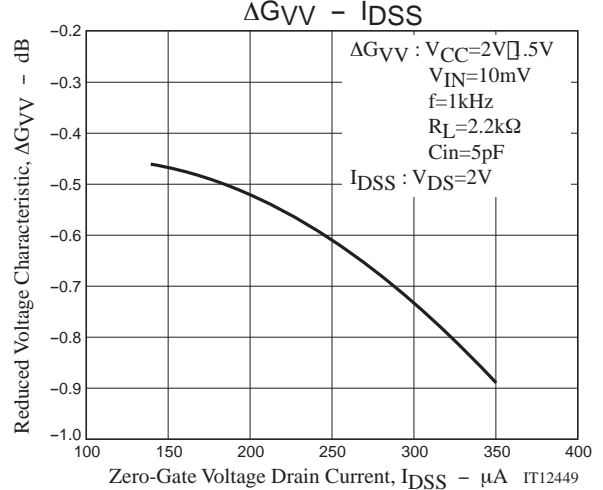
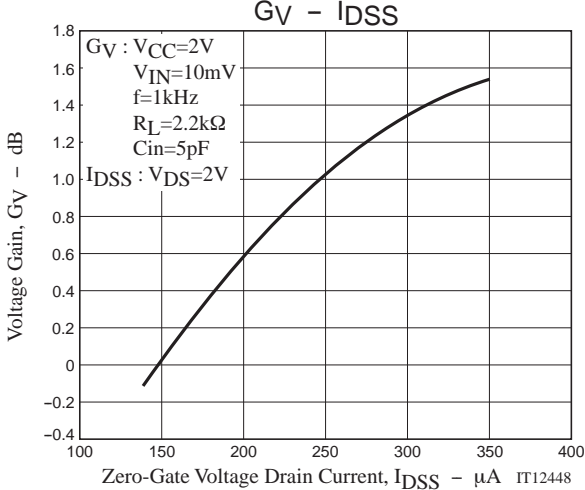
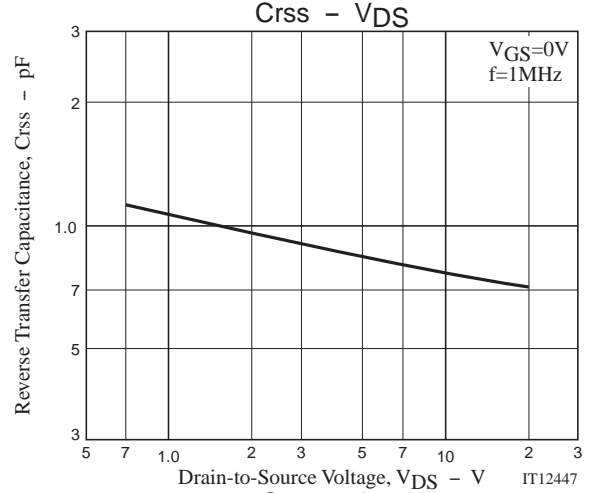
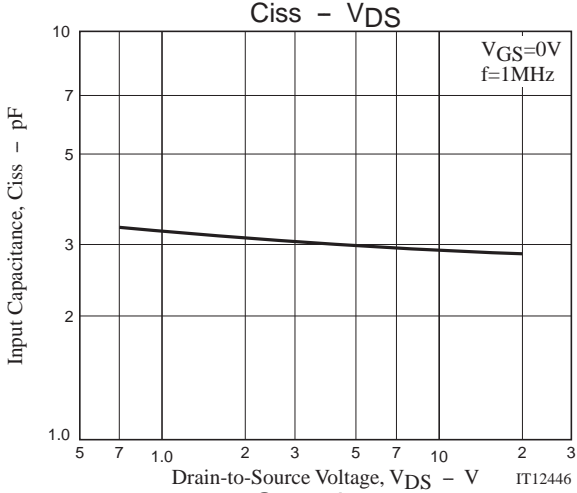
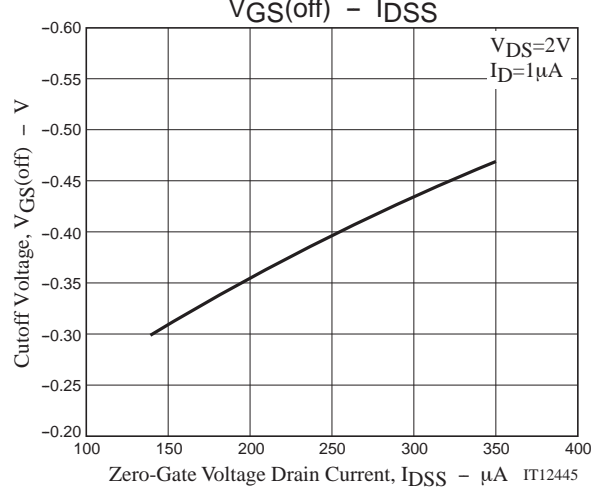
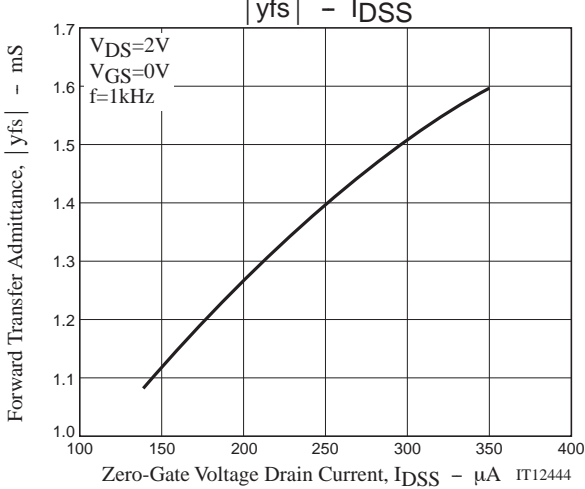
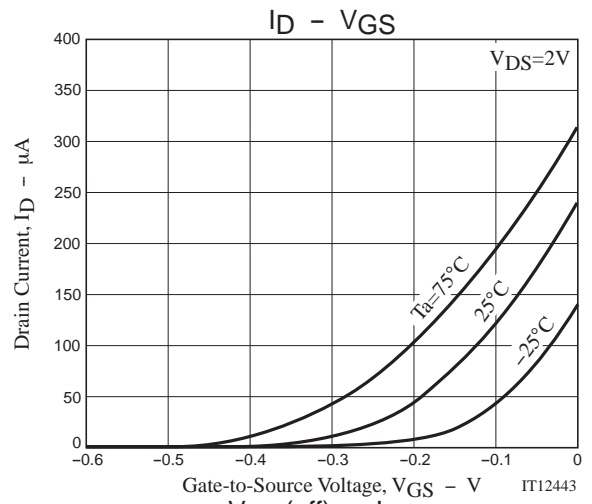
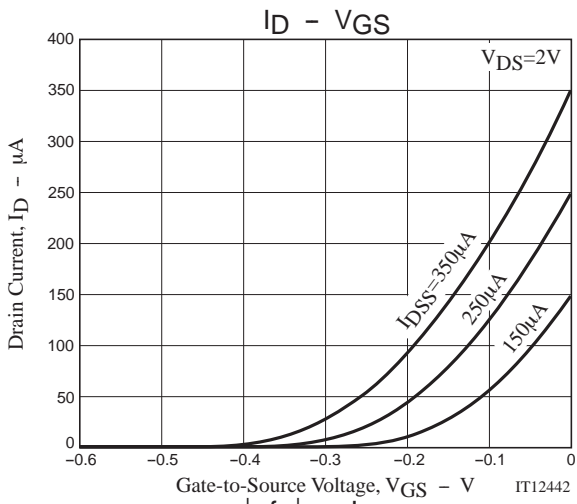
- Voltage gain
- Frequency Characteristic
- Distortion
- Reduced Voltage Characteristic

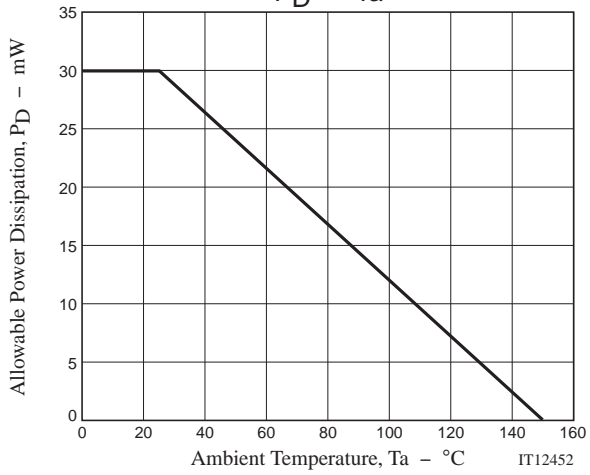
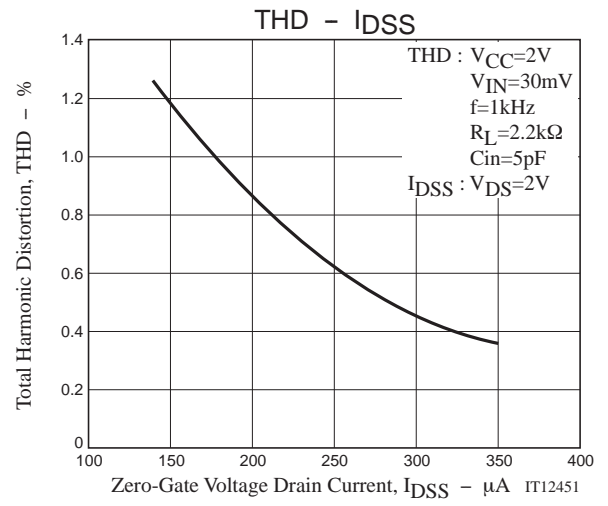
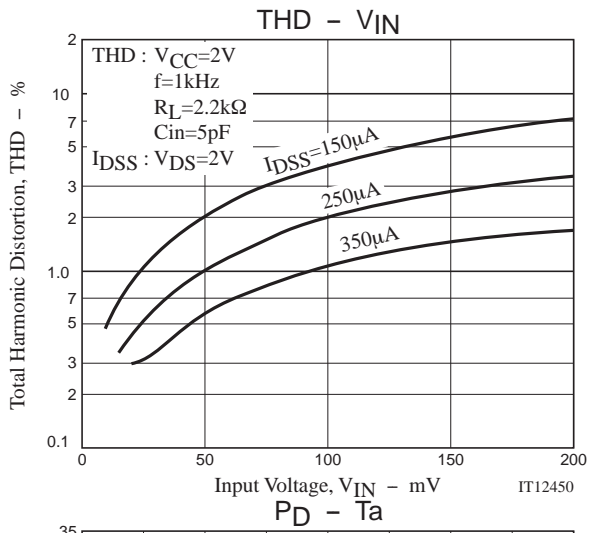


Ordering Information

Device	Package	Shipping	memo
TF252-4-TL-H	USFP	10,000pcs./reel	Pb Free and Halogen Free
TF252-5-TL-H	USFP	10,000pcs./reel	







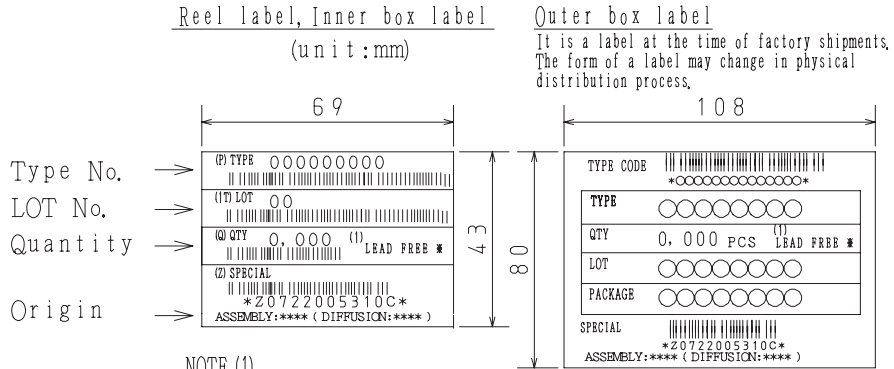
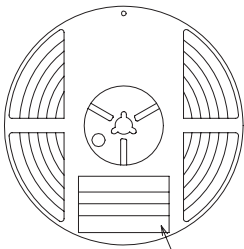
Taping Specification

TF252-4-TL-H, TF252-5-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
USFP	USFP	10,000	50,000	300,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method

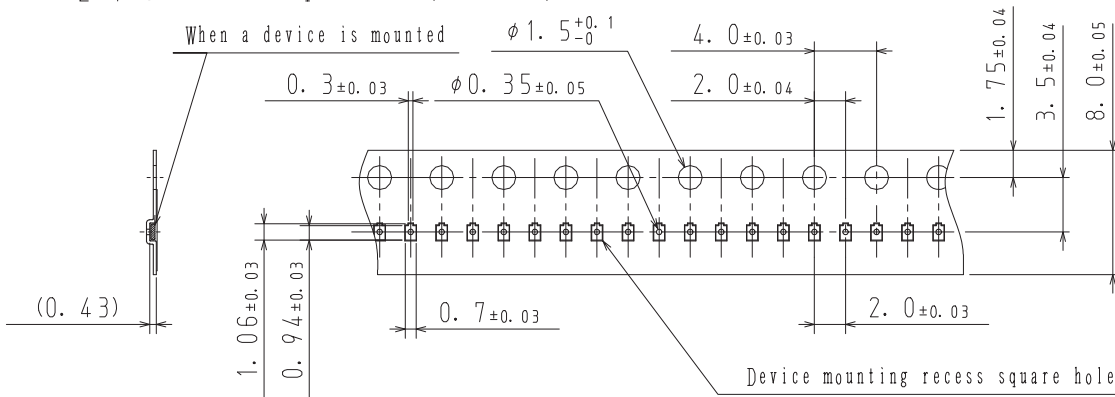


NOTE (1)
 The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

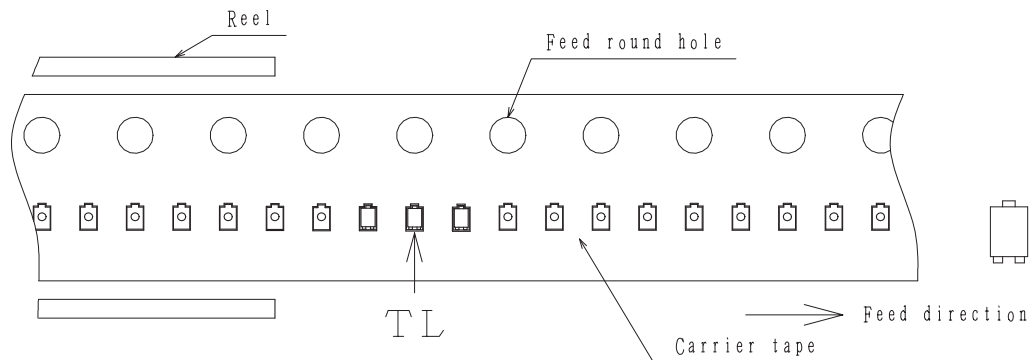
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



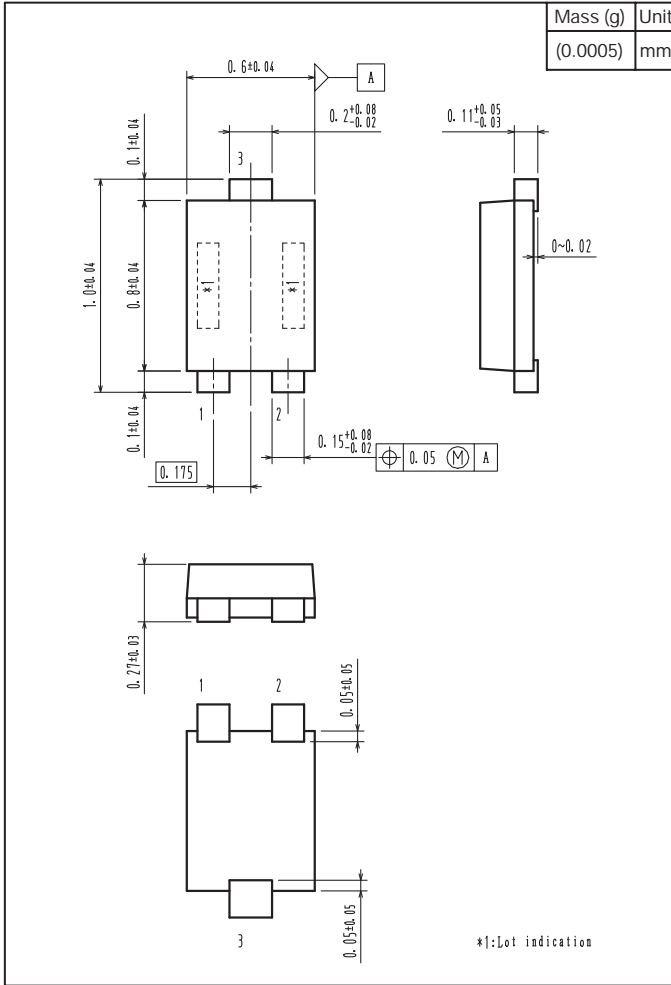
2-2. Device placement direction



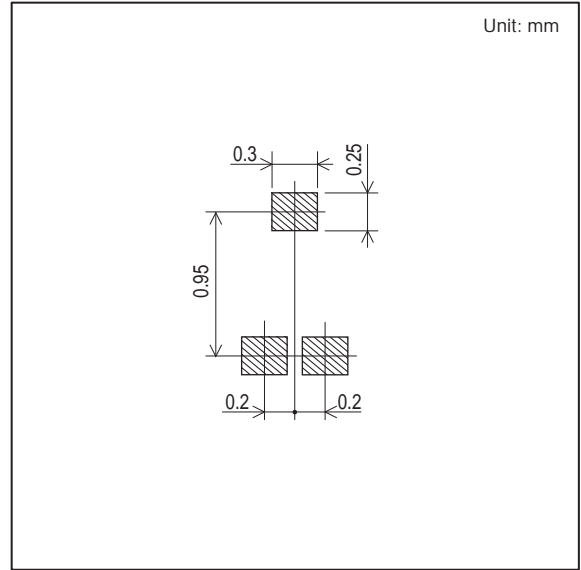
Those with one electrode terminal on the feed hole side.....TL

Outline Drawing

TF252-4-TL-H, TF252-5-TL-H



Land Pattern Example



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